Search History (12 pp.) [signature] (09/24/05).

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2418	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT;	OR	OFF	2005/09/24 19:50
L2	1	1 and (single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:02
L3	4	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti, ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:09
L4	226	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near4 (concentration content density) and interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:10
L5	4	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti, ab,clm. and interface.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:09
L6	190	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:25
L7	2	("5929259").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 20:19
L8	60	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:29

L9	3	(single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density) near6 (silicon adj carbide sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/24 20:29
S1	4	"775514".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:27
S2	6	(("6,285,064") or ("6,358,773") or ("6,368,888")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:06
S3	1	(US-20040161875-$).did.	US-PGPUB	OR	OFF	2005/04/03 22:08
S4	10	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:13
S5	2	(silicon adj carbide sic) near20 graded near20 buffer and single adj (crystalline crystal) near4 (silicon si) and (thick thickness) near10 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18
S6	2	("6750119").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/03 22:18
S7	1	"5683934".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S8	1	"5906680".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:19
S9	1	"6190975".PN.	USPAT; USOCR	OR	OFF	2005/04/03 22:20
S10	1	"20020160605".PN.	US-PGPUB	OR	OFF	2005/04/03 22:20
S11	155	junction near4 (sic silicon adj carbide) near4 (si silicon) and (monocrystalline single adj (crystal crystalline))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:50

S12	15	(US-20010015170-$).did. or (US-6472594-$ or US-6273950-$ or US-6214107-$ or US-6183857-$ or US-5861324-$ or US-5847418-$ or US-5726440-$ or US-5681402-$ or US-5671914-$ or US-5599403-$ or US-5459089-$ or US-5456762-$ or US-5449923-$).did. or (JP-62216364-$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2005/04/04 09:49
S13	144	S11 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S14	14	S12 and (interface thick thickness abrupt sharp buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 09:51
S15	7	S12 and (interface thick thickness abrupt sharp buffer) and ("SiC/Si" "Si/SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:13
S16	3	(("5298452") or ("5906680")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:01
S17	0	(257/77anduhf-cvdand("S/SiC""SiC/S")).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S18	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 10:02
S19	0	257/77 and uhf-cvd and ("S/SiC""SiC/S")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:02
S20	0	257/77 and uhf near1 cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03

S21	0	257/77 and uhf adj cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S22	0	257/77.ccls. and uhf adj cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S23	3	257/77.ccls. and uhf and cvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:03
S24	1260	((257/77) or (438/931)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:26
S25	47	S24 and ("Si/SiC" "SiC/S" interface junction) near10 (abrupt sharp)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 10:24
S26	5	S24 and hbt and buffer and graded and (thick thickness thin)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:40
S27	0	(single adj (crystalline crystal) monocrystalline) near3 (silicon "Si") near6 (silicon adj carbide "SiC") and graded near4 ("Si.sub. "$3"C.sub."$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:44
S28	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:45
S29	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and (buffer graded) near4 ("Si.sub.xC.sub.1-x" "Si.sub.1-xC.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:46
S30	0	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and "Si.sub. "$3"C.sub."$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:47

S31	363	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 11:48
S32	179	(single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") not (silicon adj carbide adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/04 12:19
S33	10	(("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306, 211")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S34	10	(("5,906,680") or ("6,190,975") or ("5,683,934") or ("20020016085") or ("6,306,211")).PN. or (2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:24
S35	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25
S36	0	(2001/0160605).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:25
S37	85	kanazawa.in. and 200210$2.pd.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S38	273	kanazawa.in. and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:26
S39	31	kanazawa.in. and silicon	US-PGPUB	OR	OFF	2005/04/04 12:31
S40	26	kanazawa.in. and silicon and substrate	US-PGPUB	OR	OFF	2005/04/04 12:26
S41	0	@pd=200210$2 and kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:31
S42	202	kanazawa.in.	US-PGPUB	OR	OFF	2005/04/04 12:32
S43	4	suemitsu.in. and sic adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53

S44	0	suemitsu.in. and nakazaka.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:53
S45	4	suemitsu.in. and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59
S46	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58
S47	2	("2001160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:58
S48	15481	nakazawa.in.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:59
S49	125	nakazawa.in. and 200210$2.pd.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:01
S50	187	nakazawa.in. and substrate	US-PGPUB	OR	OFF	2005/04/04 13:57
S51	0	(2004/0161875).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:57
S52	2	("20040161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S53	2	("200?0161875").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:58
S54	0	("20010160605").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:59

S55	0	("(monocrystallinesingleadjcrystal) near2(siliconSi)and(carbonC)and(c oncentrationprofile)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 10:25
S56	8580	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S57	1322	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S58	85	(monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) and (hbt heterojunction adj bipolar adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:27
S59	456	gated adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 12:14
S60	73	gated adj diode.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:15
S61	3	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 12:16
S62	46	boron near1 diffusion and (silicon adj carbide SiC) and concentration near3 profile and (silicon Si) near3 substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:55
S63	0	intrinsic adj buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 08:57
S64	188	buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23

S65	0	collector near4 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S66	0	collector near10 lattice and S64	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 09:23
S67	8	collector near10 lattice and S62	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:23
S68	27	(single adj crystalline monocrystalline) near2 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 10:32
S69	1	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S70	13	(single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 11:05
S71	88	polycrystalline near3 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 12:44
S72	27	polycrystalline near3 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:45
S73	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt and (carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46
S74	1	polycrystalline near3 (carbide SiC) near4 emitter and hbt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/28 12:46

S75	2	("6137120").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:09
S76	95	fang.in. and emitter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 13:10
S77	5	(("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306, 211")).PN.	US-PGPUB; USPAT	OR	OFF	2005/04/29 07:11

S78	59	(US-20010015170-$ or US-20020016085-$ or US-20020094658-$ or US-20020102862-$ or US-20020124793-$ or US-20020158311-$ or US-20020158313-$ or US-20020160605-$ or US-20020182423-$ or US-20020192918-$ or US-20030054601-$ or US-20040089918-$ or US-20040161875-$ or US-20040195655-$ or US-20040198010-$ or US-20040217430-$ or US-20050006663-$ or US-20050023642-$ or US-20050051798-$ or US-20050064645-$ or US-20050082571-$).did. or (US-5296258-$ or US-5298452-$ or US-5449923-$ or US-5456762-$ or US-5459089-$ or US-5599403-$ or US-5670414-$ or US-5671914-$ or US-5681402-$ or US-5683934-$ or US-5726440-$ or US-5847418-$ or US-5861324-$ or US-5906680-$ or US-6064081-$ or US-6183857-$ or US-6190975-$ or US-6214107-$ or US-6273950-$ or US-6285064-$ or US-6306211-$ or US-6358773-$ or US-6362065-$ or US-6368888-$ or US-6472594-$ or US-6552375-$).did. or (US-6673662-$ or US-6750119-$).did. or (JP-62216364-$).did. or (DE-3777507-$ or EP-703628-$ or EP-829908-$ or EP-908984-$ or EP-1039512-$ or US-20020016085-$ or US-6285064-$ or US-6358773-$ or US-20020102862-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/04/29 07:14
S79	0	("2andkanazawa.in.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:14
S80	0	S78 and kanazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15

S81	2	S78 and nakazawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:15
S82	2120	((257/77) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
S83	355	S82 and silicon adj carbide and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 07:31
S84	10	S82 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S85	2300	((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/04/29 08:04
S86	180	S85 NOT S82	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S87	0	S86 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/29 08:05
S88	4	"775514".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:36
S89	2	("6552375").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:54
S90	0	laser adj melting near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 16:54
S91	222	mbe near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:00

S92	121	lattice adj constant near4 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:00
S93	35	lattice adj constant near1 sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:15
S94	3	laser adj melting.ti. and (sic silicon adj carbide silicon adj germanium sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:32
S95	12	(("5906680") or ("6190975") or ("5693934") or ("6306211") or ("20020160605") or ("20020016085")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 17:33
S96	12	(("5906680") or ("6190975") or ("5683934") or ("6306211") or ("20020160605") or ("20020016085")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/24 19:50